3

3.16

For a Si bar of length $5~\mu m$, doped n-type at $10^{15}~cm^{-3}$, calculate the current density for an applied voltage of 2.5~V across its length. How about for a voltage of 2500~V? The electron and hole mobilities are $1500~cm^2/Vs$ and $500~cm^2/Vs$, respectively, in the ohmic region for electric fields below $10^4~V/cm$. For higher fields, electrons and holes have a saturation velocity of $10^7~cm/s$.

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For 2.5~V
J_x = qn\mu_n\epsilon_x
J_x = \frac{(1.6\times 10^{-19})(10^{15})(1500)(2.5)}{5\times 10^{-4}}
J_x = 1200~A/cm
For 2500~V
J_x = -qn\langle v_x \rangle
J_x = -(1.6\times 10^{-19})(10^{15})(10^7)
J_x = -1600~A/cm
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4.6

A Si sample with $10^{15}\ /cm^3$ donors is uniformly optically excited at room temperature such that $10^{19}\ /cm^3$ EHPs are generated per second. Find the separation of the quasi-Fermi levels and the change of conductivity upon shining the light. Electron and hole lifetimes are both $10\ \mu s\ D_p=12\ cm^2/s$.

4.16

A long Si sample, n-doped at $10^{17}~cm^{-3}$, with a cross-sectional area of $0.5~cm^2$ is optically excited by a laser such that $10^{20}~cm^{-3}$ EHPs are generated per second at $x=0~\mu m$. They diffuse to the right. What is the total diffusion current at $x=50~\mu m$? Electron and hole lifetimes are both $10~\mu s$. $\mu_p=500~cm^2/Vs~D_n=36~cm^2/s$.

$egin{aligned} \checkmark & \mathsf{Answer} \\ g_{op} &= 10^{20} \ cm^{-3} \\ n_0 &= 10^{17} \ cm^{-3} \\ au_n &= au_p = 10^{-5} \ s \end{aligned} \ egin{aligned} \delta p &= g_{op} au_p e^{-x/\sqrt{D_p au_p}} \\ J_p &= q rac{D_p}{L_p} g_{op} au_p e^{-x/\sqrt{D_p au_p}} \\ J_p &= 0.11733 \end{aligned} \ egin{aligned} \delta n &= g_{op} au_n e^{-x/\sqrt{D_n au_n}} \\ J_n &= q rac{D_n}{L_n} g_{op} au_n e^{-x/\sqrt{D_n au_n}} \\ J_n &= 0.23325 \end{aligned} \ I &= 0.17529 \ A \end{aligned}$